

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON) MAX}$ | I_D $T_C = +25^\circ C$ |
|---------------|-------------------------|------------------------------|
| -40V | 11mΩ @ $V_{GS} = -10V$ | -50A |
| | 15mΩ @ $V_{GS} = -4.5V$ | -40A |

Description and Applications

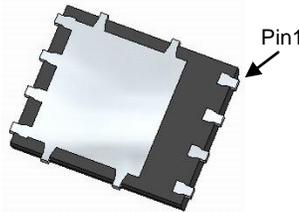
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Analog Switch

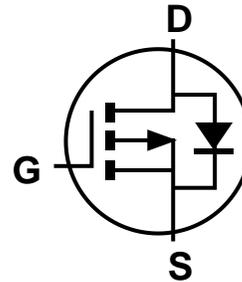
POWERDI®5060-8



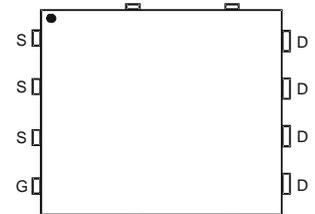
Top View



Bottom View



Internal Schematic


 Top View
Pin Configuration

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

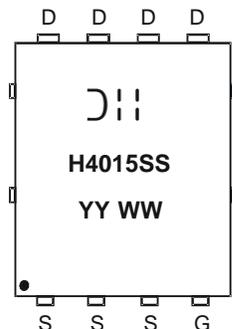
- Case: POWERDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|----------------|----------------|---------------------|
| DMPH4015SPS-13 | POWERDI®5060-8 | 2,500 / Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



D D D D = Manufacturer's Marking
 H4015SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 15 = 2015)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|--|--------------|---|------------------|---------------|-------|
| Drain-Source Voltage | | | V _{DSS} | -40 | V |
| Gate-Source Voltage | | | V _{GSS} | ±25 | V |
| Continuous Drain Current (Note 6) V _{GS} = -10V | Steady State | T _C = +25°C T _C = +100°C | I _D | -50 -35 | A |
| | Steady State | T _A = +25°C T _A = +100°C | I _D | -12.0 -9.0 | A |
| Pulsed Drain Current (10μs pulse, duty cycle = 1%) | | | I _{DM} | -100 | A |
| Maximum Body Diode Continuous Current (Note 6) | | | I _S | -5.5 | A |
| Avalanche Current (Note 7) L = 1mH | | | I _{AS} | -22 | A |
| Avalanche Energy (Note 7) L = 1mH | | | E _{AS} | 260 | mJ |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units |
|--|------------------------|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5) | T _A = +25°C | P _D | 1.5 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | R _{θJA} | 98 | °C/W |
| Total Power Dissipation (Note 6) | T _A = +25°C | P _D | 2.6 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | R _{θJA} | 57.0 | °C/W |
| Thermal Resistance, Junction to Case | | R _{θJC} | 0.9 | °C/W |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +175 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|------|------|------|------|--|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -40 | — | — | V | V _{GS} = 0V, I _D = -250μA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | -1 | μA | V _{DS} = -40V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±25V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -1.5 | -2 | -2.5 | V | V _{DS} = V _{GS} , I _D = -250μA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 8 | 11 | mΩ | V _{GS} = -10V, I _D = -9.8A |
| | | — | 11 | 15 | | V _{GS} = -4.5V, I _D = -9.8A |
| Diode Forward Voltage | V _{SD} | — | -0.7 | -1 | V | V _{GS} = 0V, I _S = -1A |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C _{iSS} | — | 4234 | — | pF | V _{DS} = -20V, V _{GS} = 0V f = 1MHz |
| Output Capacitance | C _{oSS} | — | 1036 | — | | |
| Reverse Transfer Capacitance | C _{rSS} | — | 526 | — | | |
| Gate Resistance | R _g | — | 7.8 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1MHz |
| Total Gate Charge (V _{GS} = -4.5V) | Q _g | — | 42.7 | — | nC | V _{DS} = -20V, I _D = -9.8A |
| Total Gate Charge (V _{GS} = -10V) | Q _g | — | 91 | — | | |
| Gate-Source Charge | Q _{gs} | — | 14.2 | — | | |
| Gate-Drain Charge | Q _{gd} | — | 13.5 | — | | |
| Turn-On Delay Time | t _{D(ON)} | — | 13.2 | — | ns | V _{GS} = -10V, V _{DD} = -20V, R _G = 6Ω, I _D = -1A |
| Turn-On Rise Time | t _r | — | 10 | — | | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 303 | — | | |
| Turn-Off Fall Time | t _f | — | 138 | — | | |
| Reverse Recovery Time | t _{RR} | — | 26 | — | ns | I _F = -9.8A, di/dt = -100A/μs |
| Reverse Recovery Charge | Q _{RR} | — | 20 | — | nC | I _F = -9.8A, di/dt = -100A/μs |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

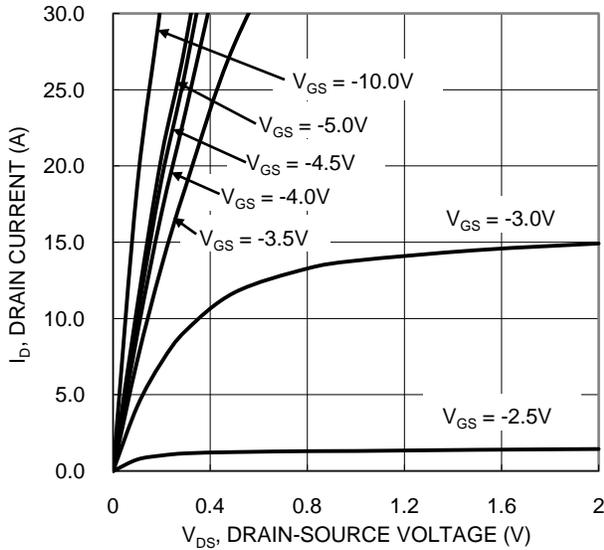


Figure 1. Typical Output Characteristic

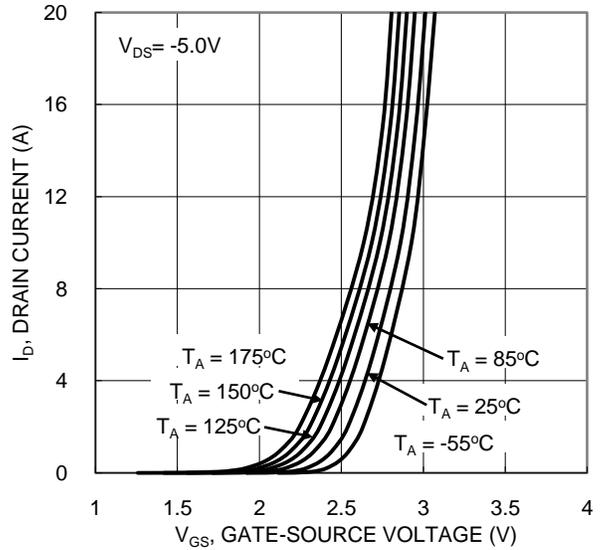


Figure 2. Typical Transfer Characteristic

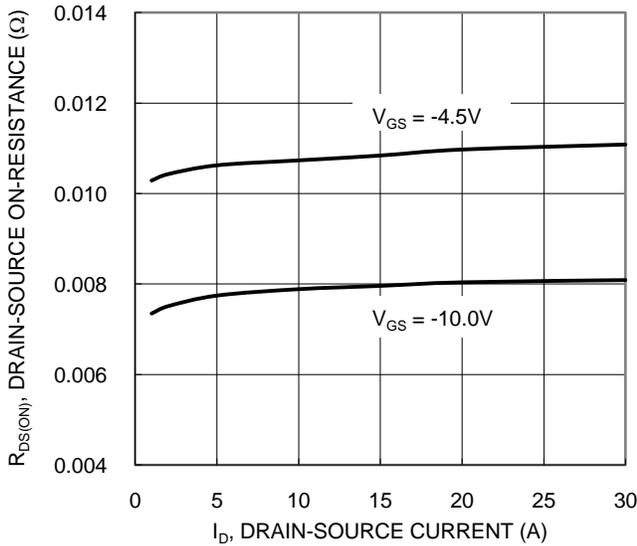


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

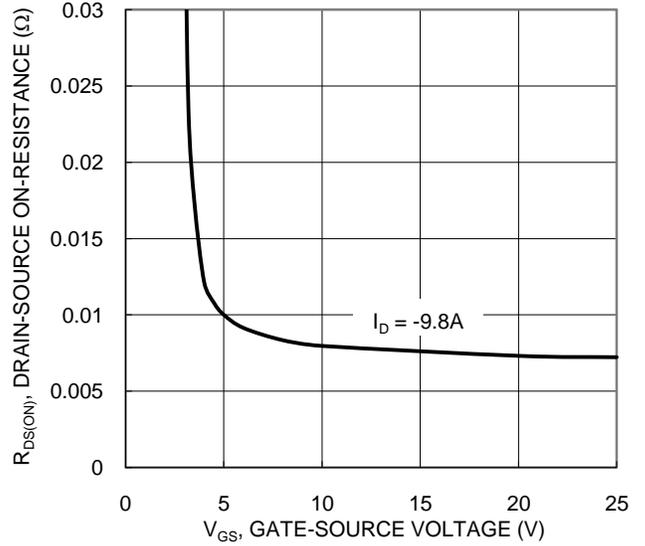


Figure 4. Typical Transfer Characteristic

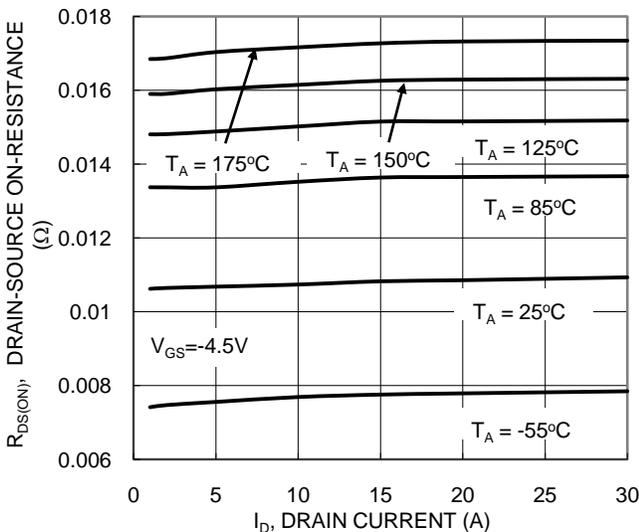


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

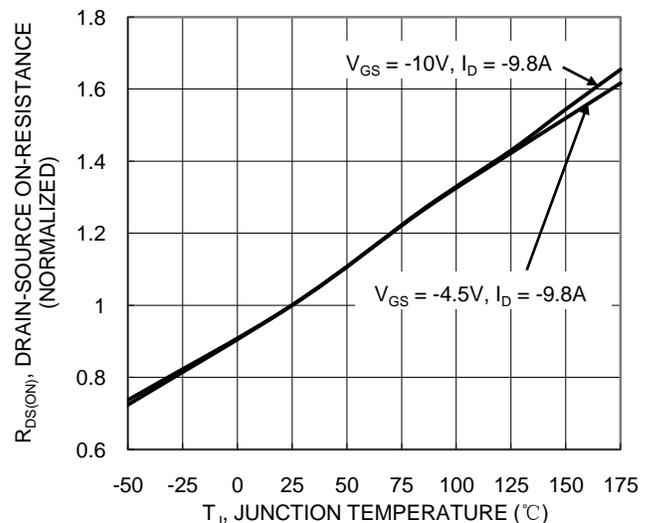


Figure 6. On-Resistance Variation with Temperature

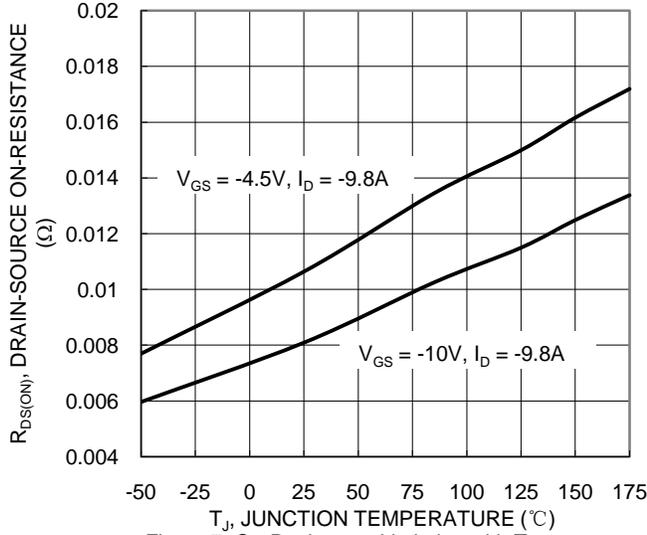


Figure 7. On-Resistance Variation with Temperature

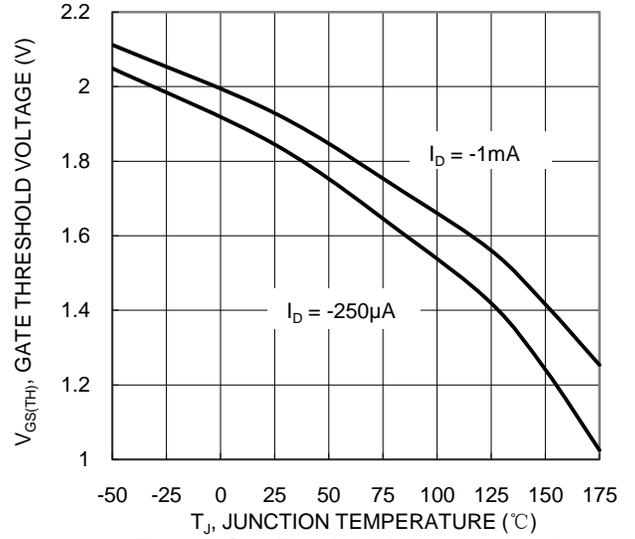


Figure 8. Gate Threshold Variation vs. Junction Temperature

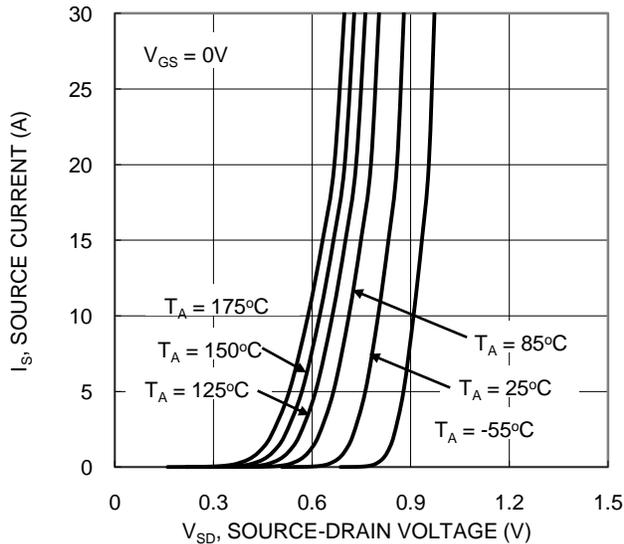


Figure 9. Diode Forward Voltage vs. Current

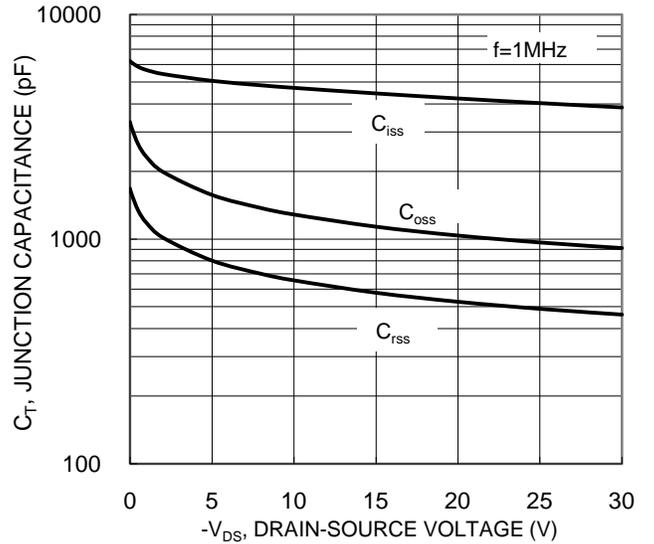


Figure 10. Typical Junction Capacitance

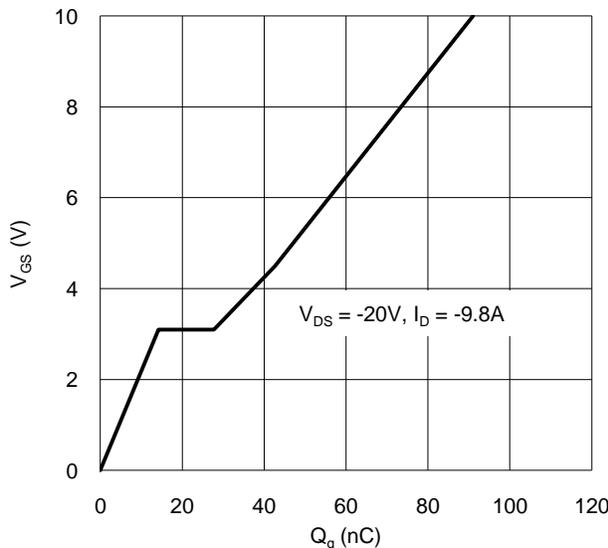


Figure 11. Gate Charge

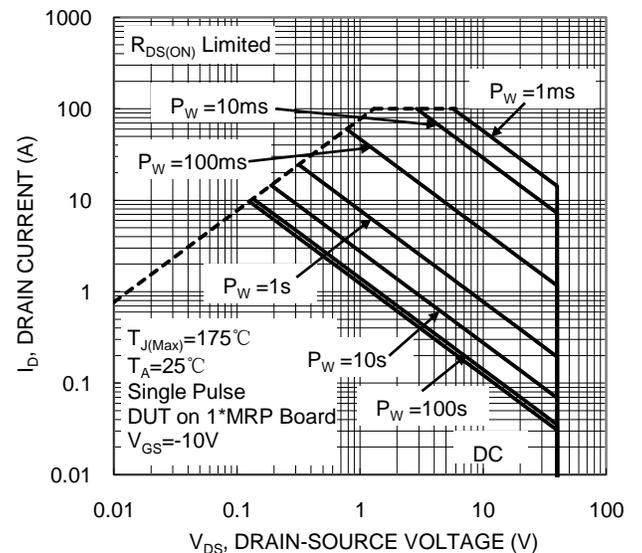


Figure 12. SOA, Safe Operation Area

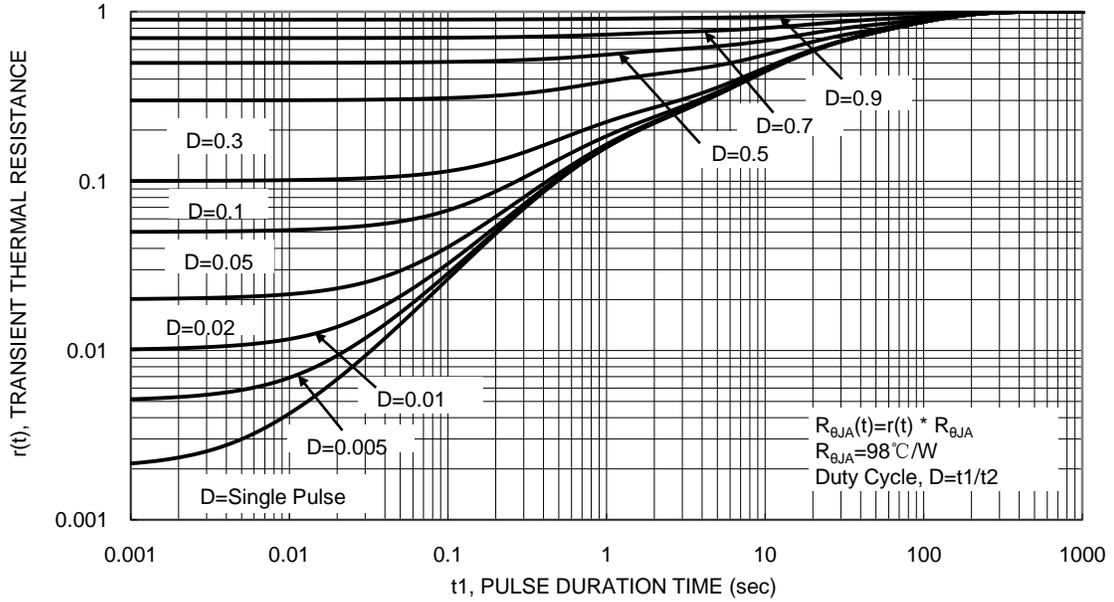
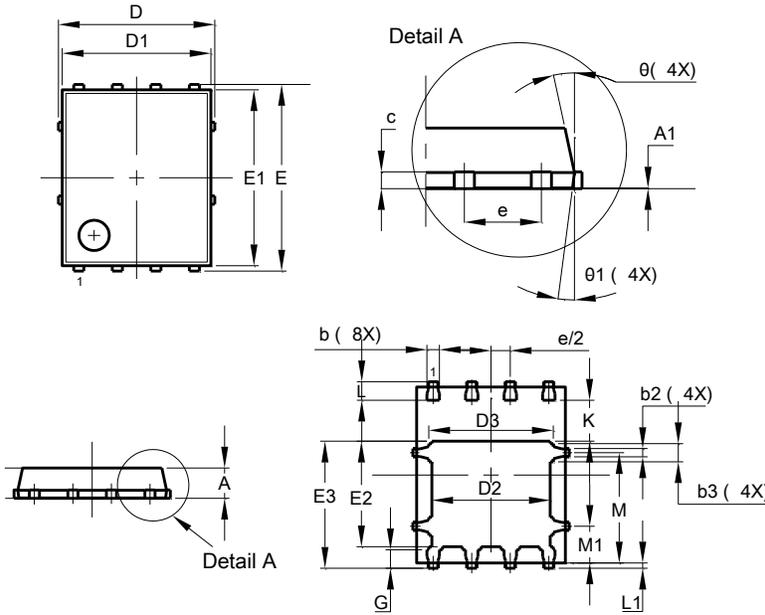


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

POWERDI® 5060-8

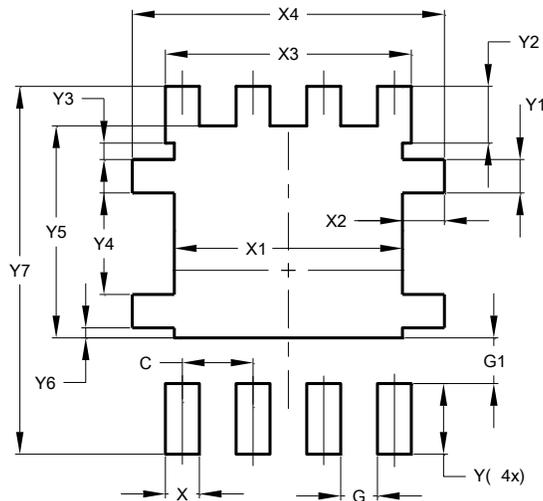


| POWERDI® 5060-8 | | | |
|----------------------|----------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.90 | 1.10 | 1.00 |
| A1 | 0.00 | 0.05 | — |
| b | 0.33 | 0.51 | 0.41 |
| b2 | 0.200 | 0.350 | 0.273 |
| b3 | 0.40 | 0.80 | 0.60 |
| c | 0.230 | 0.330 | 0.277 |
| D | 5.15 BSC | | |
| D1 | 4.70 | 5.10 | 4.90 |
| D2 | 3.70 | 4.10 | 3.90 |
| D3 | 3.90 | 4.30 | 4.10 |
| E | 6.15 BSC | | |
| E1 | 5.60 | 6.00 | 5.80 |
| E2 | 3.28 | 3.68 | 3.48 |
| E3 | 3.99 | 4.39 | 4.19 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.71 | 0.61 |
| K | 0.51 | — | — |
| L | 0.51 | 0.71 | 0.61 |
| L1 | 0.100 | 0.200 | 0.175 |
| M | 3.235 | 4.035 | 3.635 |
| M1 | 1.00 | 1.40 | 1.21 |
| θ | 10° | 12° | 11° |
| $\theta1$ | 6° | 8° | 7° |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

POWERDI® 5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| X | 0.610 |
| X1 | 4.100 |
| X2 | 0.755 |
| X3 | 4.420 |
| X4 | 5.610 |
| Y | 1.270 |
| Y1 | 0.600 |
| Y2 | 1.020 |
| Y3 | 0.295 |
| Y4 | 1.825 |
| Y5 | 3.810 |
| Y6 | 0.180 |
| Y7 | 6.610 |

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